

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	96126	(tft or (thin near film near transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/09 16:40
L2	23065	(tft or (thin near film near transistor)) and (gate near (insulating or insulation) near (film or layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/09 16:40
L3	887	(tft or (thin near film near transistor)) and (first near gate near (insulating or insulation) near (film or layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/09 16:41
L4	633	(tft or (thin near film near transistor)) and (first near gate near (insulating or insulation) near (film or layer)) and (second near gate near (insulating or insulation) near (film or layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/09 16:41
L5	347	(tft or (thin near film near transistor)) same (first near gate near (insulating or insulation) near (film or layer)) and (second near gate near (insulating or insulation) near (film or layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/09 16:41
L6	303	(tft or (thin near film near transistor)) same (first near gate near (insulating or insulation) near (film or layer)) same (second near gate near (insulating or insulation) near (film or layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/09 16:42
L7	242	(tft or (thin near film near transistor)) same (first near gate near (insulating or insulation) near (film or layer)) with (second near gate near (insulating or insulation) near (film or layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/09 16:42
L8	58	((tft or (thin near film near transistor)) same (first near gate near (insulating or insulation) near (film or layer)) with (second near gate near (insulating or insulation) near (film or layer))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/09 16:42

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L9		37	(US-20050121673-\$ or US-20030042542-\$ or US-20040048422-\$ or US-20010052950-\$).did. or (US-5599729-\$ or US-6222214-\$ or US-5196912-\$ or US-5266515-\$ or US-6777716-\$ or US-6534826-\$ or US-6576924-\$ or US-6191442-\$ or US-6452241-\$ or US-5545584-\$ or US-5374570-\$ or US-6140684-\$ or US-5291053-\$ or US-6133609-\$ or US-6864134-\$ or US-5429968-\$ or US-5309010-\$ or US-6576926-\$ or US-6624473-\$ or US-6303966-\$ or US-5219779-\$ or US-5576243-\$ or US-6603453-\$ or US-5793059-\$ or US-6489632-\$ or US-5334863-\$).did. or (US-6693324-\$ or US-5547892-\$ or US-5291440-\$ or US-6462723-\$ or US-4984040-\$).did. or (US-20050161673-\$ or JP-07092500-\$).did.	US-PGPUB; USPAT; DERWENT	OR	ON	2006/10/09 16:46
L10		13	I9 and (first near gate near (insulation or insulating) near (film or layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/09 16:47
L11		13	I9 and (first near gate near (insulation or insulating) near (film or layer)) with (first near gate near (insulation or insulating) near (film or layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/09 16:47
L12		7	I9 and (first near gate near (insulation or insulating) near (film or layer)) with (second near gate near (insulation or insulating) near (film or layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/09 16:47